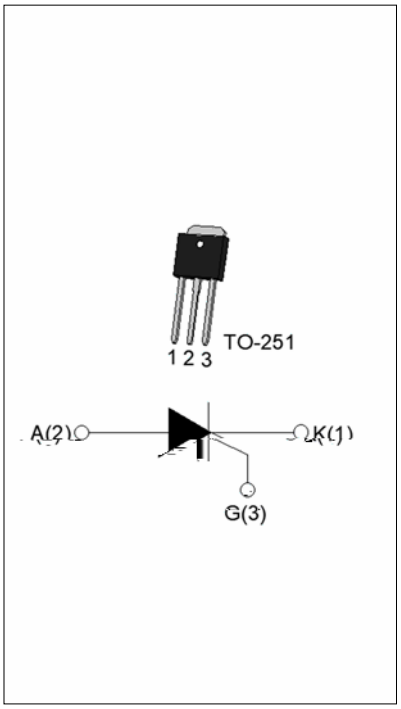
JCT816HH 16A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT816HH of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.
Package TO-251 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	≤15	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	800	V
Average on-state current ($T_C \leq$ 132)	$I_{T(AV)}$	10	A
RMS on-state current ($T_C \leq$ 132)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (t_p=10ms, T_j=25)	I_{TSM}	150	A
Non repetitive surge peak on-state current (t_p=8.3ms, T_j=25)		165	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	113	A^2s
Critical rate of rise of on-state current (I_G=2 × I_{GT}, f=100Hz , T_j=150)	dI/dt	150	A/μs
Peak gate current (t_p=20μs , T_j=150)	I_{GM}	5	A

FIG.1: Maximum power dissipation versus RMS on-state current

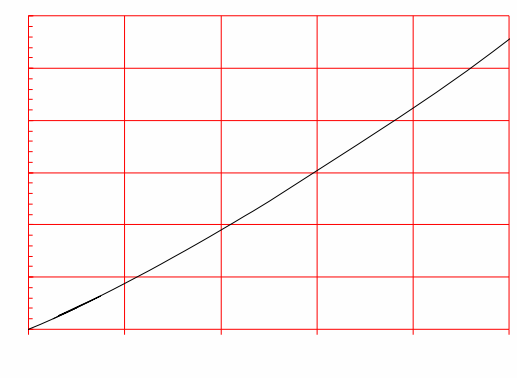
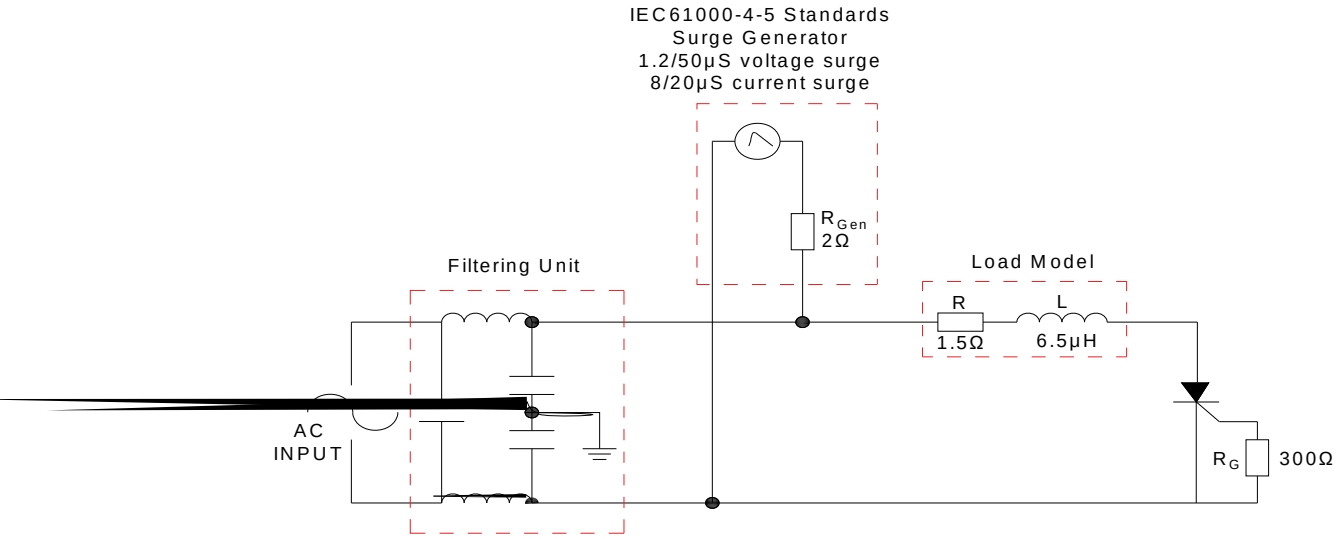


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



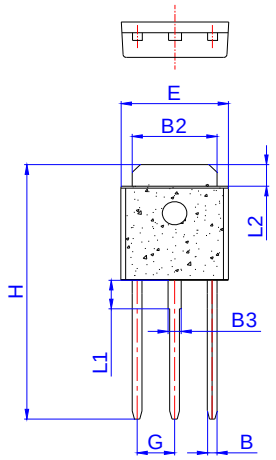
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT816HH	800	15	TO-251	80	Tube

Document Revision History

Date	Revision	Changes
Jun.15, 2023	A.1.0	Last update
Oct.17, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Dimensions

Information furnished in this doc